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#### **Inclosure Material:**

Metal

**Overall Length:** 

1.308 inches

# **Mounting Facility Quantity:**

1

## Internal Configuration:

Junction contact

## Electrode Internally-electrically Connected To Case:

Anode

#### **Mounting Method:**

Threaded stud

Features Provided:

Hermetically sealed case

#### **Overall Width Across Flats:**

Between 0.424 inches and 0.437 inches

#### Thread Size:

0.190 inches

## Semiconductor Material:

Silicon

# Voltage Rating In Volts Per Characteristic:

50.0 repetitive peak reverse voltage and 50.0 repetitive peak off-state voltage and 10.0 peak gate voltage

## **Current Rating Per Characteristic:**

4.70 amperes forward current, average absolute

## Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air

## **Special Features:**

Junction pattern arrangement: pnpn

## **Test Data Document:**

81349-mil-prf-19500/168 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

## **Thread Series Designator:**

Unf

## **Terminal Type And Quantity:**

2 tab, solder lug and 1 threaded stud

## **Specification Data:**

81349-mil-prf-19500/168 government specification

# Shelf Life:

N/a

- Unit Of Measure:
- ---
- Demilitarization:
- No

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Fiig: A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.